

### Features:

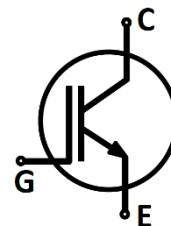
- 650V Trench & field stop technology
- Low switching losses
- High short circuit capability
- Positive Temperature coefficient
- Easy paralleling

### Recommended for:

power modules

### Applications:

drives



### Mechanical parameters

|                                  |                   |                  |                 |
|----------------------------------|-------------------|------------------|-----------------|
| Die size                         | $L \times W$      | 11.50×8.20       | mm <sup>2</sup> |
| Emitter pad size                 | $L \times W$      | See chip drawing | mm <sup>2</sup> |
| Gate pad size                    | $L \times W$      | 1.31×0.80        | mm <sup>2</sup> |
| Silicon thickness                |                   | 80               | μm              |
| Wafer size                       |                   | 200              | mm              |
| Maximum possible chips per wafer |                   | 274              |                 |
| Passivation frontside            |                   | Polyimide        |                 |
| Pad Metallization                | AlCu              | 4                | μm              |
| Backside Metallization           | Al / Ti / Ni / Ag | 1.7              | μm              |

### Maximum Ratings

| Parameters                                                                              | Symbol        | Value            | Unit |
|-----------------------------------------------------------------------------------------|---------------|------------------|------|
| Collector-emitter voltage                                                               | $V_{CE}$      | 650              | V    |
| DC collector current, limited by $T_{vj\ max}$                                          | $I_C$         | 200 <sup>1</sup> | A    |
| Pulsed collector current, $t_p$ limited by $T_{vj\ max}$ <sup>2</sup>                   | $I_{C\ puls}$ | 600              | A    |
| Gate-emitter voltage                                                                    | $V_{GE}$      | ±20              | V    |
| Operating junction temperature                                                          | $T_{vj\ op}$  | -40~175          | °C   |
| Storage temperature                                                                     | $T_{stg}$     | -40~150          | °C   |
| Short circuit data <sup>3</sup> ( $V_{GE}=15V$ , $V_{CC}=360V$ , $T_{vj}=150^\circ C$ ) | $t_{sc}$      | 10               | μs   |

### Static Characteristic ( $T_{vj}=25^\circ C$ , unless otherwise noted)

| Parameter                            | Symbol        | Conditions                       | Min. | Typ. | Max. | Unit |
|--------------------------------------|---------------|----------------------------------|------|------|------|------|
| Collector-emitter breakdown voltage  | $V_{(BR)CES}$ | $V_{GE}=0V$ ,<br>$I_C=25\mu A$   | 650  | -    | -    | V    |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $V_{GE}=15V$ ,<br>$I_C=25A$      | 0.80 | 0.90 | 1.00 | V    |
| Gate-emitter threshold voltage       | $V_{GE(th)}$  | $I_C=3.2mA$ ,<br>$V_{CE}=V_{GE}$ | 4.3  | 4.8  | 5.3  | V    |
| Collector-emitter leakage            | $I_{CES}$     | $V_{CE}=650V$ ,<br>$V_{GE}=0V$   | -    | -    | 1.08 | μA   |
| Gate-emitter leakage                 | $I_{GES}$     | $V_{CE}=0V$ ,<br>$V_{GE}=20V$    | -    | -    | 120  | nA   |
| Integrated gate resistor             | $R_{Gint}$    |                                  |      | 2.0  |      | Ω    |

<sup>1</sup> Depending on thermal properties of assembly.

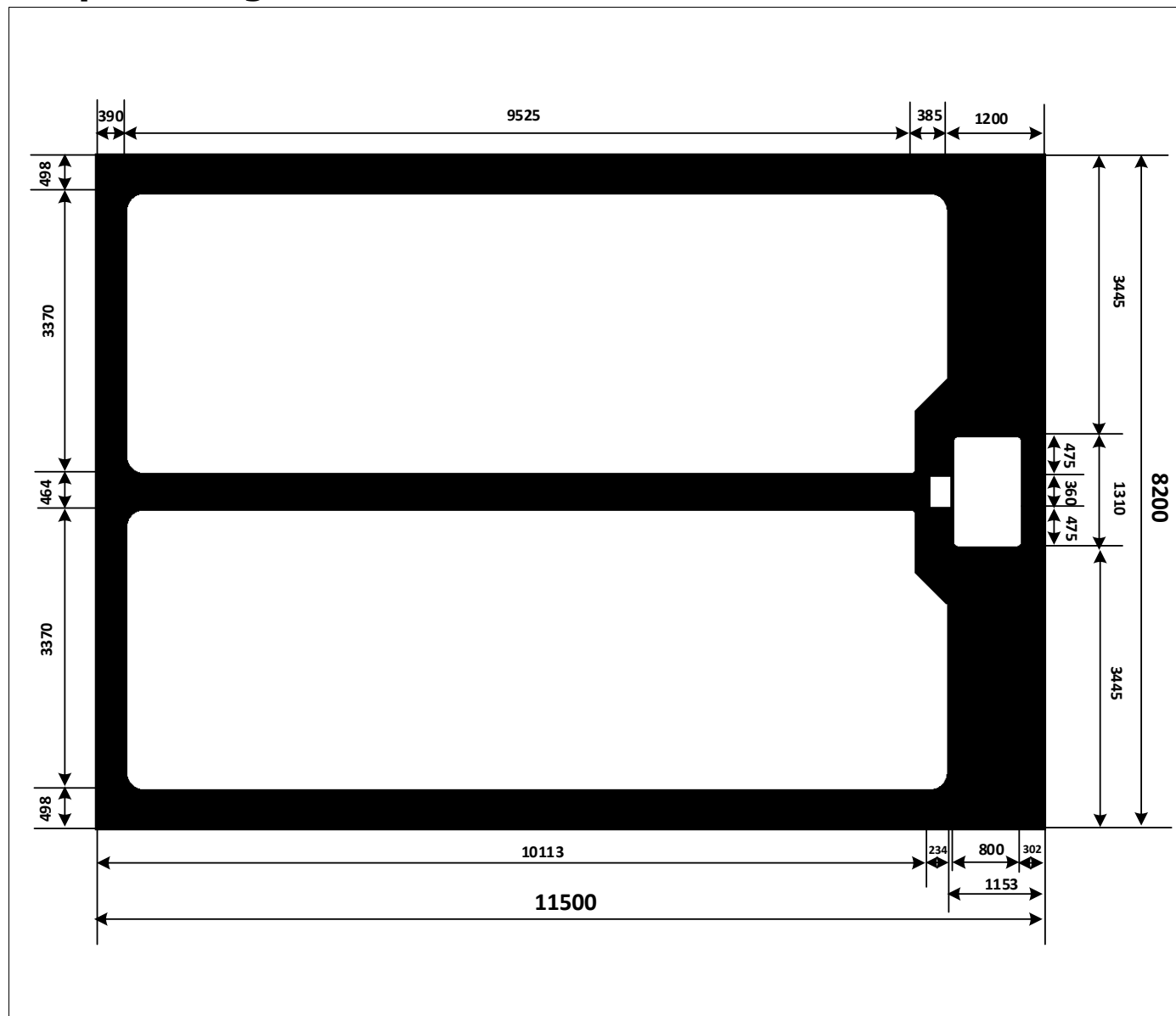
<sup>2</sup> Not subject to production test - verified by design/characterization.

<sup>3</sup> Allowed number of short circuit: <1000; time between short circuit: >1s.

## Electrical Characteristic <sup>1</sup>

| Parameter                            |                              | Symbol        | Conditions                                                                                  | Min. | Typ.  | Max. | Unit |
|--------------------------------------|------------------------------|---------------|---------------------------------------------------------------------------------------------|------|-------|------|------|
| Collector-emitter saturation voltage | $T_{vj}=25^{\circ}\text{C}$  | $V_{CE(sat)}$ | $V_{GE}=15\text{V},$<br>$I_C=200\text{A}$                                                   | 1.30 | 1.50  | 1.70 | V    |
|                                      | $T_{vj}=150^{\circ}\text{C}$ |               |                                                                                             | 1.40 | 1.70  | 2.00 |      |
| Input capacitance                    |                              | $C_{ies}$     | $V_{CE}=25\text{V},$<br>$V_{GE}=0\text{V}, f=100\text{kHz},$<br>$T_{vj}=25^{\circ}\text{C}$ | -    | 14400 | -    | pF   |
| Reverse transfer capacitance         |                              | $C_{res}$     |                                                                                             | -    | 280   | -    | pF   |

### Chip Drawing (unit: $\mu\text{m}$ )



<sup>1</sup> Not subject to production test - verified by design/characterization.

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